

Technological realization of a hybrid photovoltaic-thermoelectric system

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Technological realization of a hybrid photovoltaicthermoelectric system

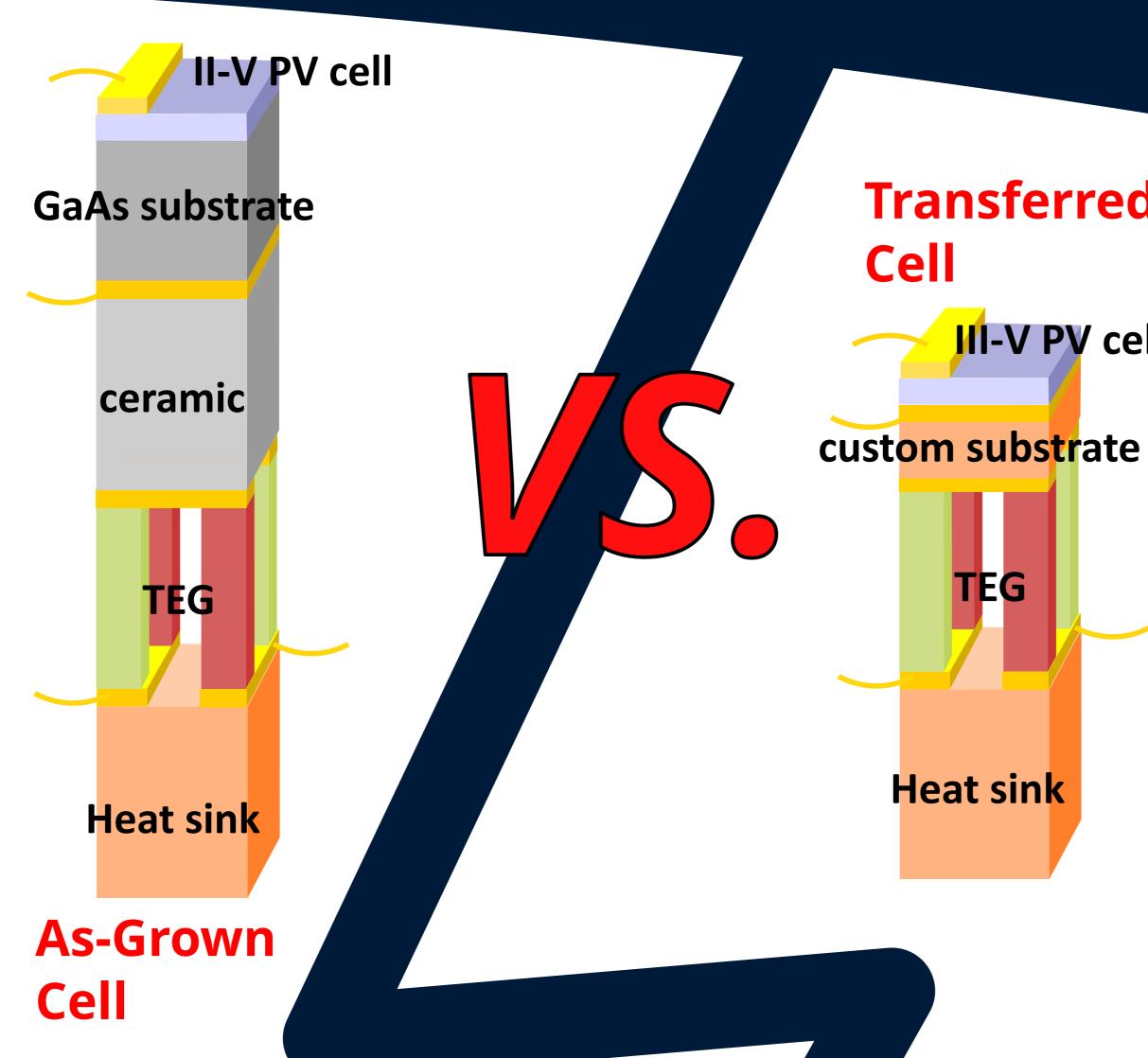
Léopold BOUDIER, Sebastien HANAUER, Jean-Baptiste DOUCET, Rodolphe VAILLON, Guilhem ALMUNEAU, Inès REVOL

Context

- One way of harvesting heat dissipated in a photovoltaic (PV) cell is by combination with a thermoelectric generator (TEG) in a hybrid energy device

How to fabricate such a system?

- We compare here a standard solar cell fabrication process with one that allows us to reduce thermal resistance between the PV cell and the heat sink.



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Challenges III-V PV cell

Transferred

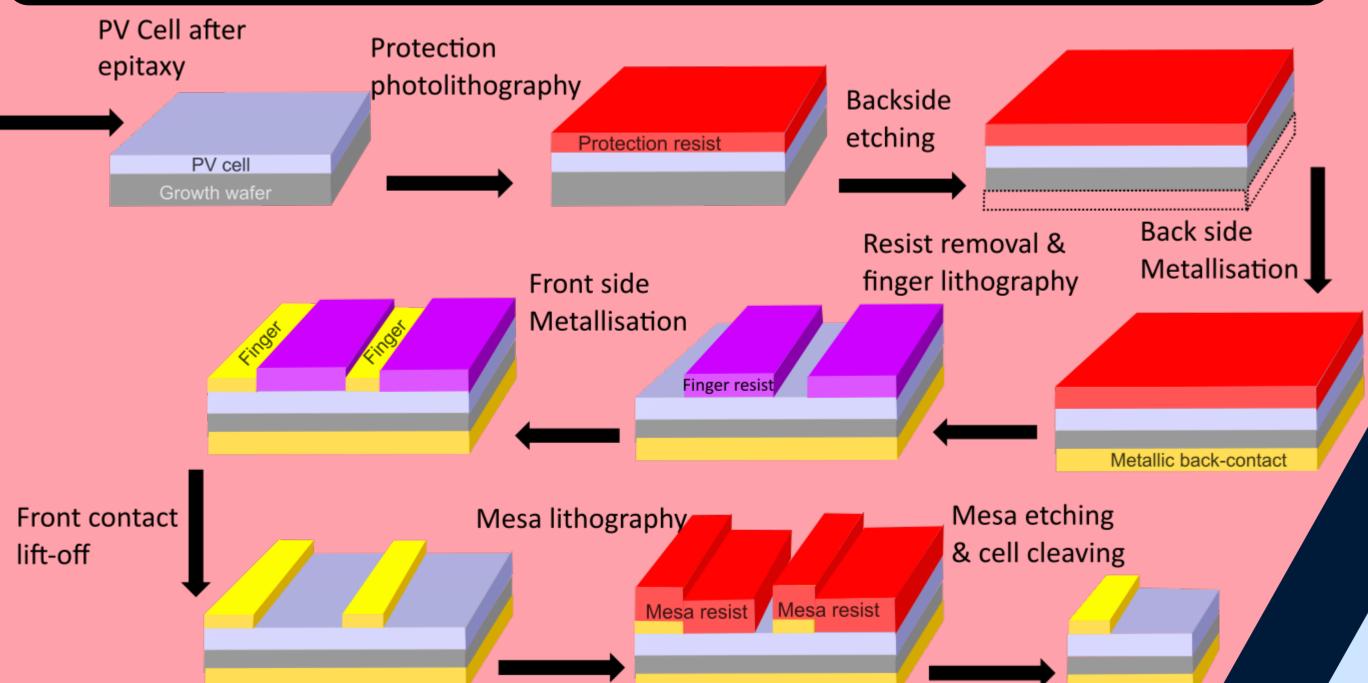
Heat sink

Cell

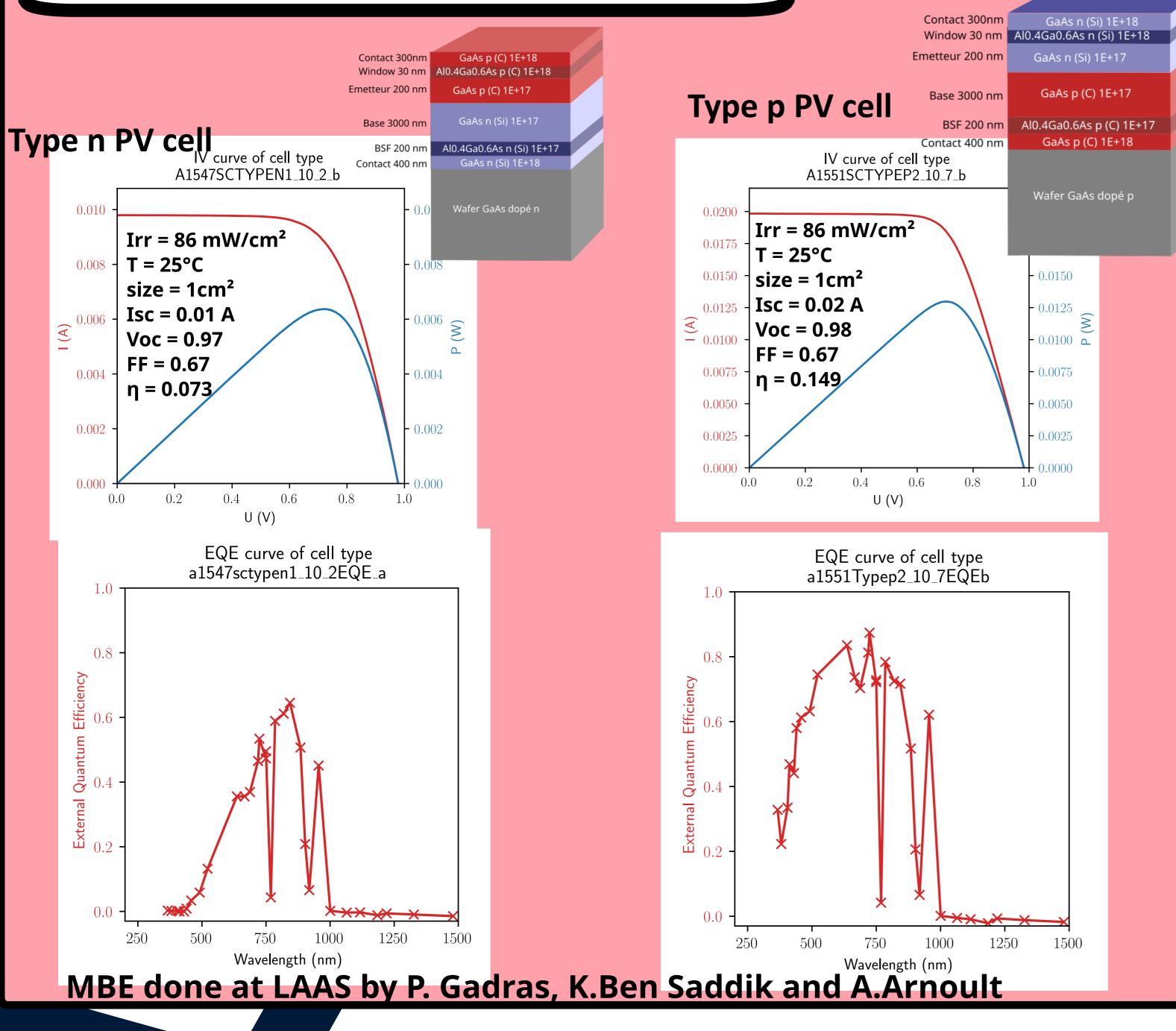
The process allowing us to transfer the III-V PV cell on a thinner copper substrate includes 3 main challenges:

- The full removal of the GaAs substrate via selective wet etching NH4OH: H2O2
- A **bonding** method that can **hold above 300°C** for further bonding steps.
- Annealing of the contact at higher temperature than usual.

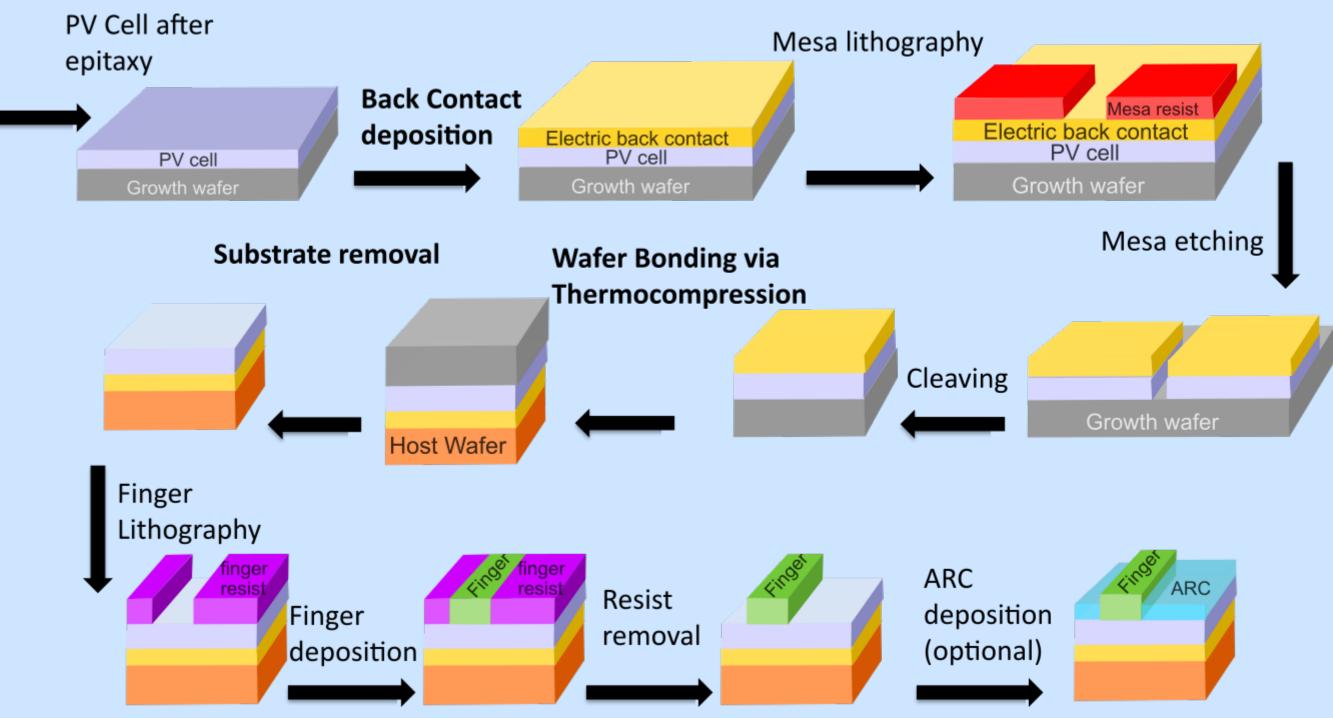
Standard process for solar cell fabrication



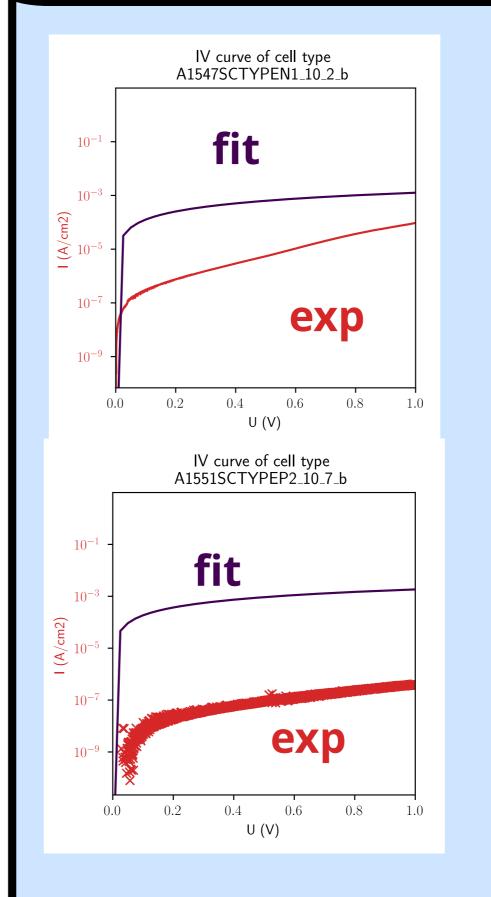
Fabrication of the reference cell



Process for transfering on custom substrate



Double diode model



In our case, solar cells efficiency is limited by series resistances. => Caused by metal -

semiconductor contacts

Use of the double diode model on dark IV curves to determine the origin of power losses

Question: How to fit properly transcendental equation for this model?

$$J = J_{01}exp\left[rac{q(V-JR_s)}{kT}
ight] + J_{02}exp\left[rac{q(V-JR_s)}{2kT}
ight] + rac{V-JR_s}{R_{shunt}}$$

Conclusion

- Comparison between custom and as-grown substrate process
- Electrical characterisation of cells with as-grown substrate
- Modelling of the cell to identify limiting factors for efficiency

All these aspects could pave the way toward a **better** understanding of PV-TE devices and the design of a fully optimized system





